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**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as

follows:

IN THE CLAIMS:

Please add new claims 21 through 24 as follows:

--21. The semiconductor device in accordance with claim 12, wherein

said part of said insulating film having a width being smaller than the minimum working

formable by photolithography.

22. The semiconductor device in accordance with claim 21, wherein

a side surface of said capacitor lower electrode has a curved plane.

23. The semiconductor device in accordance with claim 21, wherein

said insulating film includes an upper insulating film and a lower insulating film being

different in etching rate from each other.

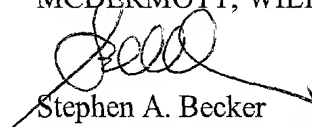
24. The semiconductor device in accordance with claim 21, comprising:  
said capacitor upper electrode being formed to extend toward said peripheral circuit region,  
an upper interlayer isolation film being formed on said capacitor upper electrode and having a contact hole exposing a surface of said capacitor upper electrode, and  
a peripheral circuit element protection film being formed under said insulating film in a region located under said contact hole.--

#### REMARKS

Entry of this preliminary amendment is respectfully requested.

Respectfully submitted,

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